

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- **High-Frequency Operation**
- Temperature-Independent Switching •
- Extremely Fast Switching •

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway •

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters •



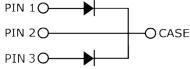
Part Number	Package	Qty(PCS)		
HIDW30G120C5B	TO247-3L	30		

Maximum Ratings (T_c=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	1200	v		
V _{RSM}	Surge Peak Reverse Voltage	1300	V		
V _R	DC Peak Reverse Voltage	1200	V		
I _F	Continuous Forward Current (Per Leg/Device)	44/88 21.5/43 15/30	А	T _c =25°C T _c =135°C T _c =152°C	Fig. 3
I _{FRM}	Repetitive Peak Forward Surge Current	68* 44*	А	T _c =25°C, t _p =10 ms, Half Sine Pulse T _c =110°C, t _p =10 ms, Half Sine Pulse	
I _{FSM}	Non-Repetitive Forward Surge Current	100* 85*	А	T _c =25°C, t _p =10 ms, Half Sine Pulse T _c =110°C, t _p =10 ms, Half Sine Pulse	Fig. 8
$\mathbf{I}_{\mathrm{F,Max}}$	Non-Repetitive Peak Forward Current	900* 750*	A	T _c =25°C, t _p =10 ms, Pulse T _c =110°C, t _p =10 ms, Pulse	Fig. 8
P _{tot}	Power Dissipation (Per Leg/Device)	220/440 95/190	w	T _c =25°C T _c =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V _R =0-960V	
∫i²dt	i²t value	50* 36*	A²s	T _c =25°C, t _p =10 ms T _c =110°C, t _p =10 ms	
TJ	Operating Junction Range	-55 to +175	°C		
T _{stg}	Storage Temperature Range	-55 to +135	°C		
	TO-247 Mounting Torque	1	Nm Ibf-in	M3 Screw 6-32 Screw	

* Per Leg, ** Per Device









Electrical Characteristics (Per Leg)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.6 2.3	1.8 3	V	I _F = 15 A T_=25°C I _F = 15 A T_=175°C	Fig. 1
I _R	Reverse Current	35 120	200 300	μA	V _R = 1200 V T _J =25°C V _R = 1200 V T _J =175°C	Fig. 2
Q _c	Total Capacitive Charge	77.5		nC	V _R = 800 V, I _F = 15A d <i>i</i> /d <i>t</i> = 200 A/μs T _J = 25°C	Fig. 5
С	Total Capacitance	1200 70 50		pF	V _R = 0 V, T _J = 25°C, f = 1 MHz V _R = 400 V, T _J = 25°C, f = 1 MHz V _R = 800 V, T _J = 25°C, f = 1 MHz	Fig. 6
E _c	Capacitance Stored Energy	22.1		μJ	V _R = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Тур.	Unit	Note
R _{ejc}	R _{eJC} Thermal Resistance from Junction to Case		°C/W	Fig. 9

** Per Device, * Per Leg

Typical Performance (Per Leg)

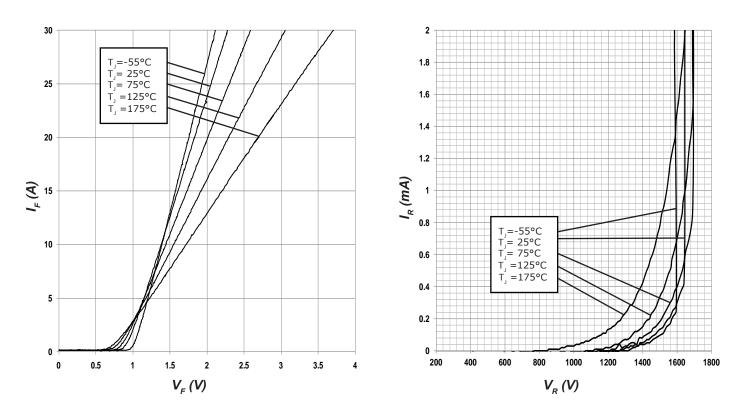


Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics



Typical Performance (Per Leg)

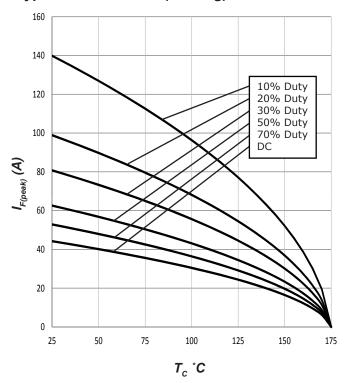
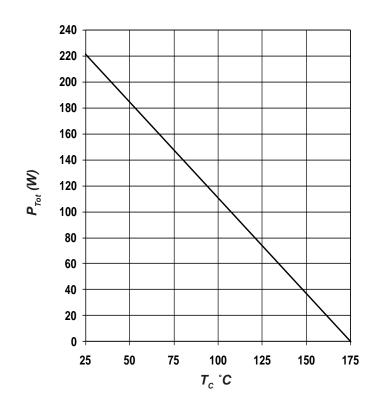
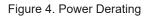


Figure 3. Current Derating





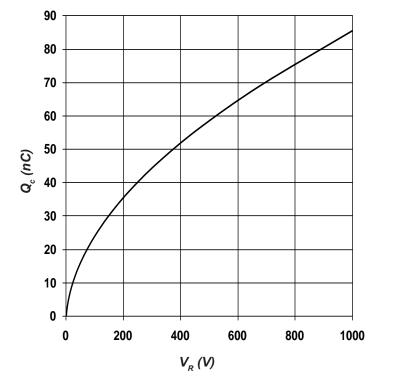


Figure 5. Recovery Charge vs. Reverse Voltage

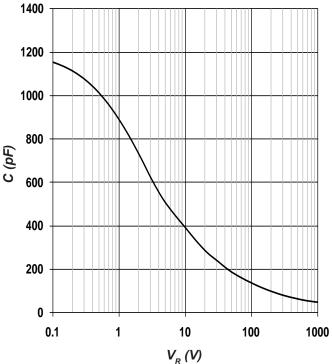
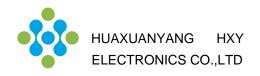


Figure 6. Capacitance vs. Reverse Voltage



Typical Performance

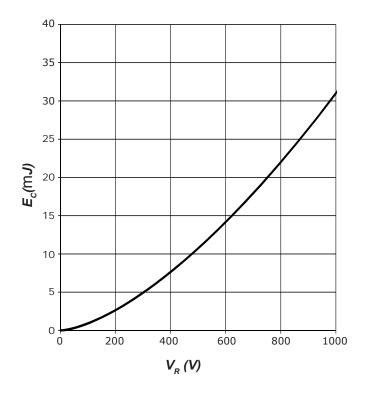


Figure 7. Typical Capacitance Stored Energy, per leg

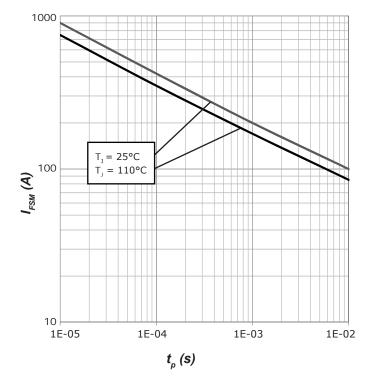


Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform), per leg

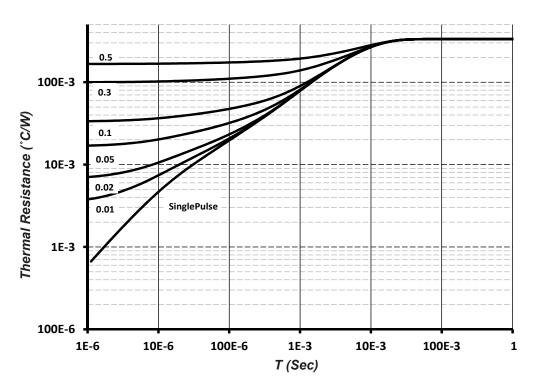
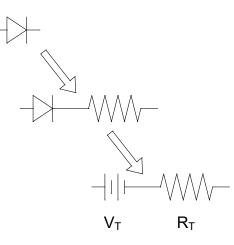


Figure 9. Device Transient Thermal Impedance



Diode Model

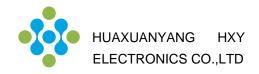


$$Vf_T = V_T + If * R_T$$

 $V_T = 0.97 + (T_j * -2.12*10^{-3})$

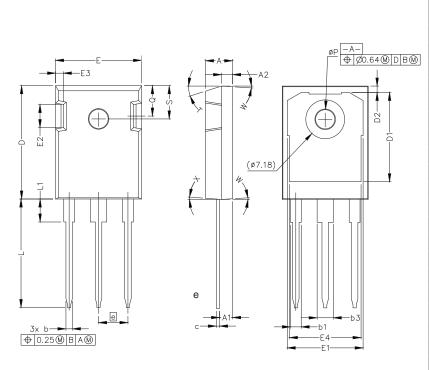
$$R_{T} = 0.031 + (T_{j} * 3.92*10^{-4})$$

Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

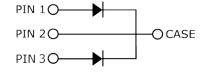


Package Dimensions

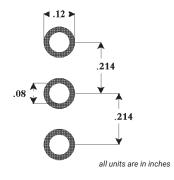
Package TO247-3L

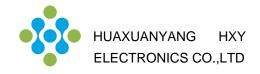


POS	Inc	hes	Millimeters		
F03	Min Max		Min	Max	
А	.190	.205	4.83	5.21	
A1	.090	.100	2.29	2.54	
A2	.075	.085	1.91	2.16	
b	.042	.052	1.07	1.33	
b1	.075	.095	1.91	2.41	
b3	.113	.133	2.87	3.38	
С	.022	.027	0.55	0.68	
D	.819	.831	20.80	21.10	
D1	.640	.695	16.25	17.65	
D2	.037	.049	0.95	1.25	
E	.620	.635	15.75	16.13	
E1	.516	.557	13.10	14.15	
E2	.145	.201	3.68	5.10	
E3	.039	.075	1.00	1.90	
E4	.487	.529	12.38	13.43	
е	.214	BSC	5.44 BSC		
L	.780	.800	19.81	20.32	
L1	.161	.173	4.10	4.40	
Ν	3				
ØP	.138	.144	3.51	3.65	
Q	.216	.236	5.49	6.00	
S	.238	.248	6.04	6.30	
Т	17.5° REF				
W	3.5° REF				
Х	4° REF				



Recommended Solder Pad Layout





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